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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SK1337

Silicon N-Channel MOS FET

RENESAS

ADE-208-1274 (Z)

1st. Edition

Mar. 2001

Application

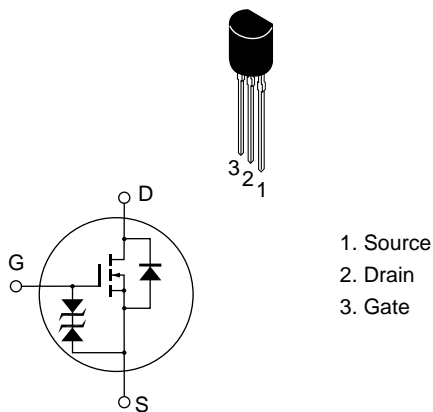
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device
 - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

Outline

TO-92



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	100	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current	I_D	0.3	A
Drain peak current	$I_{D(pulse)}^{*1}$	1.2	A
Body to drain diode reverse drain current	I_{DR}	0.3	A
Channel dissipation	Pch	400	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

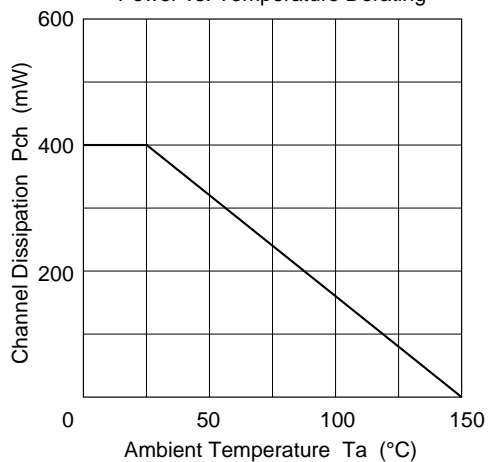
Note: 1. PW ≤ 10 μs, duty cycle ≤ 1%

Electrical Characteristics (Ta = 25°C)

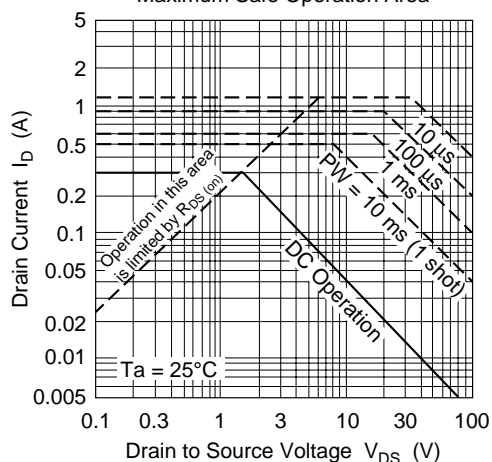
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	50	μA	$V_{DS} = 80 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	3.5	4.5	Ω	$I_D = 0.2 \text{ A}$, $V_{GS} = 10 \text{ V}^{*1}$
		—	4.0	6.5	Ω	$I_D = 0.2 \text{ A}$, $V_{GS} = 4 \text{ V}^{*1}$
Forward transfer admittance	yfs	0.22	0.35	—	S	$I_D = 0.2 \text{ A}$, $V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	Ciss	—	35	—	pF	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$
Output capacitance	Coss	—	14	—	pF	
Reverse transfer capacitance	Crss	—	3.5	—	pF	
Turn-on delay time	$t_{d(on)}$	—	2	—	ns	$I_D = 0.2 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_L = 150 \text{ }\Omega$
Rise time	t_r	—	4	—	ns	
Turn-off delay time	$t_{d(off)}$	—	17	—	ns	
Fall time	t_f	—	15	—	ns	
Body to drain diode forward voltage	V_{DF}	—	0.9	—	V	$I_F = 0.3 \text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	80	—	ns	$I_F = 0.3 \text{ A}$, $V_{GS} = 0$, $di_F/dt = 50 \text{ A}/\mu\text{s}$

Note: 1. Pulse test

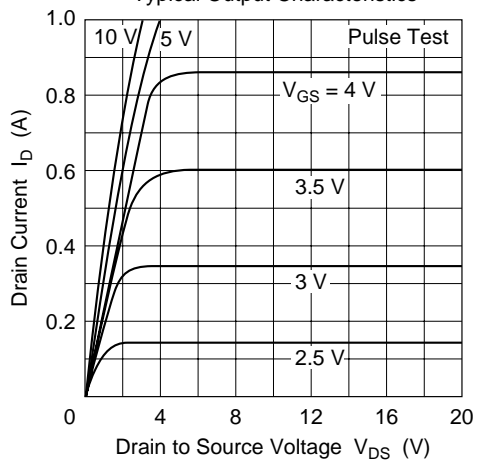
Power vs. Temperature Derating



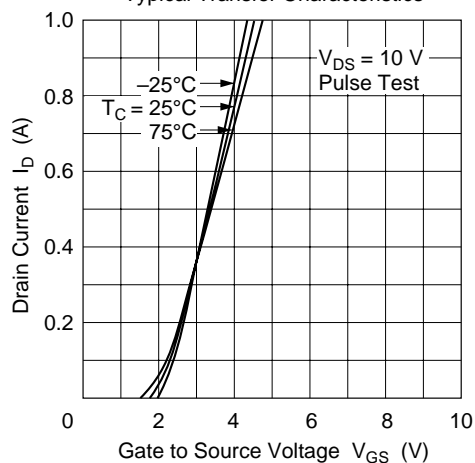
Maximum Safe Operation Area

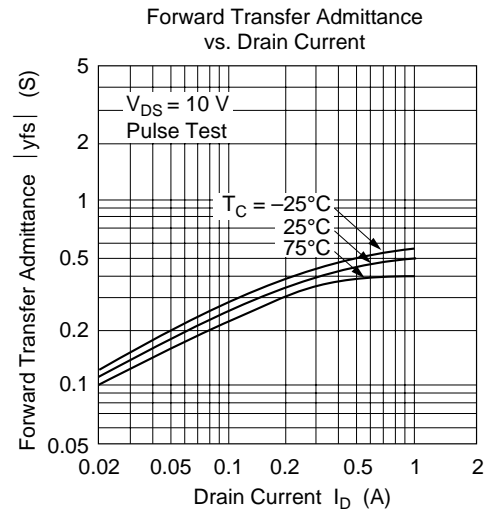
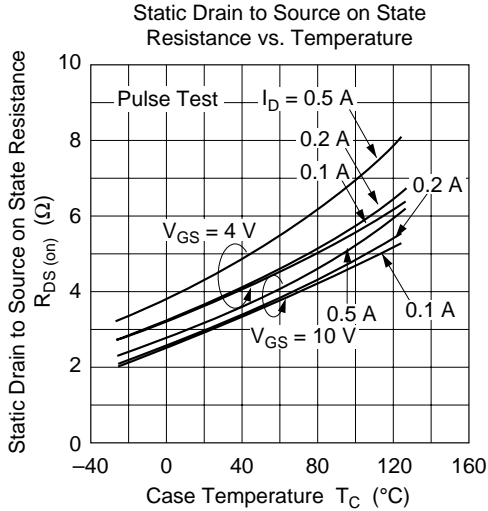
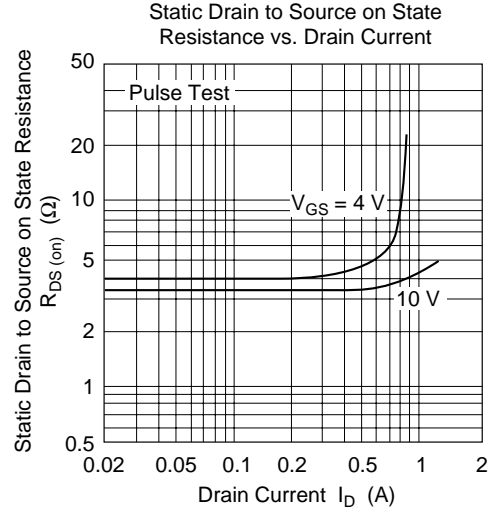
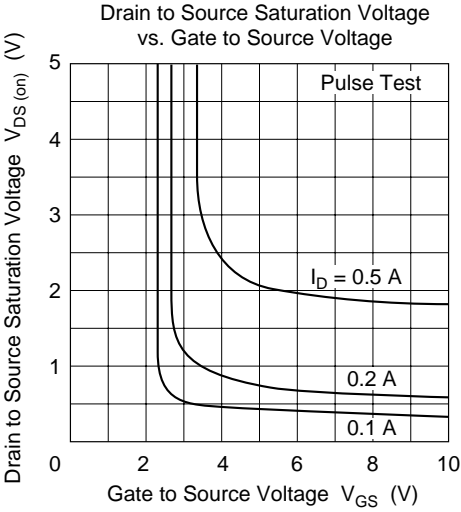


Typical Output Characteristics

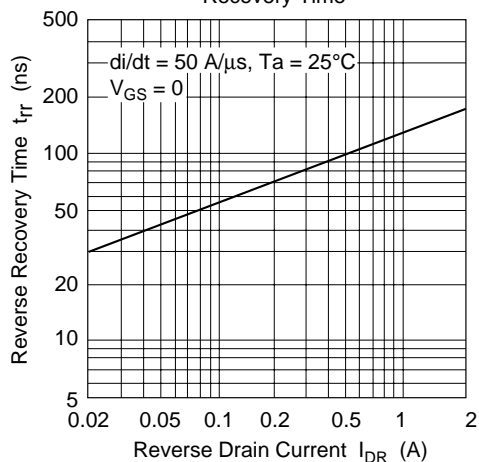


Typical Transfer Characteristics

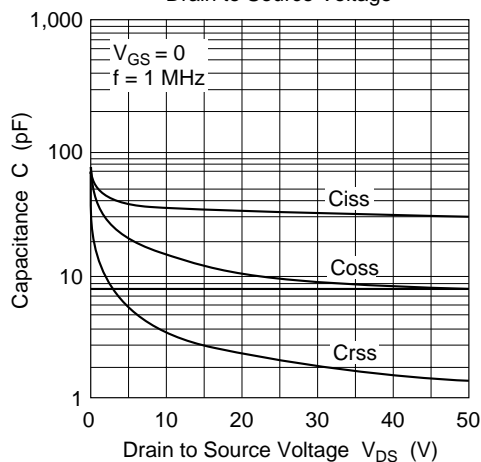




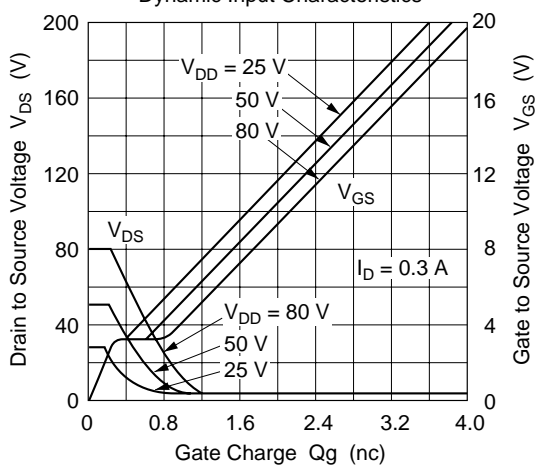
Body to Drain Diode Reverse
Recovery Time



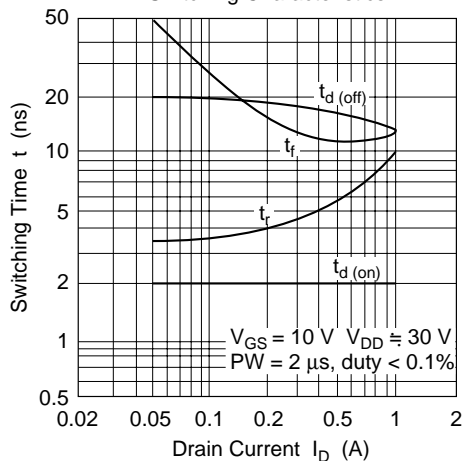
Typical Capacitance vs.
Drain to Source Voltage

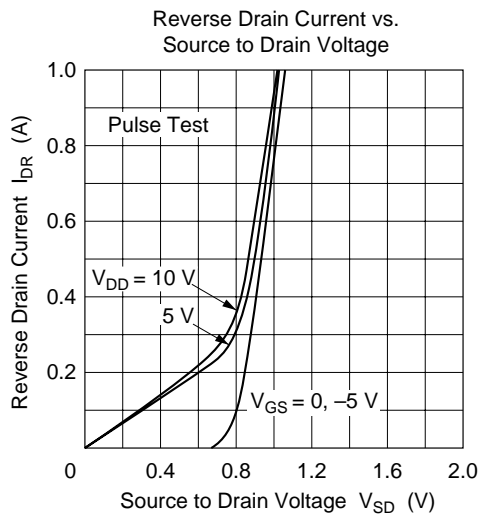


Dynamic Input Characteristics



Switching Characteristics

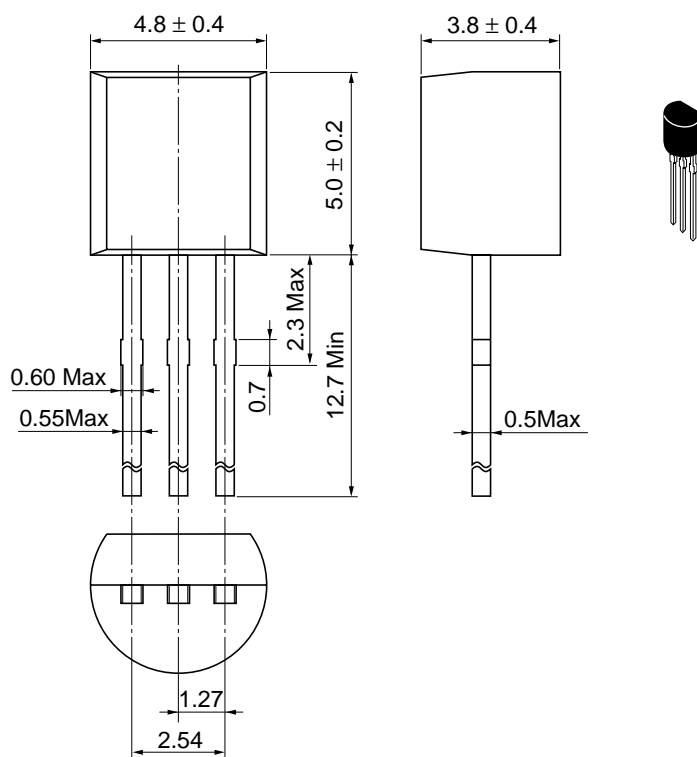




Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.25 g

Cautions

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